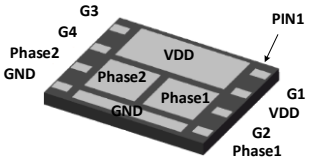
GOOD-ARK SEMICONDUCTOR

GSMP0364

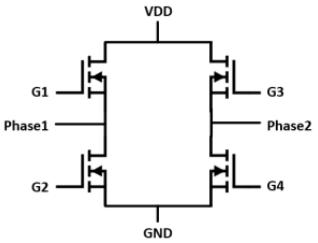
30V 4 IN 1 N-Channel MOSFETs

Main Product Characteristics

BV_{DSS}	30V
$R_{DS(ON)}$	5.5mΩ
I_D	64A



DFN5x6



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for full bridge applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSMP0364 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous (T_C=25°C)	I_D	64	A
Drain Current-Continuous (T_C=100°C)		40.5	
Drain Current-Pulsed[1]	I_{DM}	256	A
Single Pulse Avalanche Energy[2]	E_{AS}	88	mJ
Single Pulse Avalanche Current[2]	I_{AS}	42	A
Power Dissipation (T_C=25°C)	P_D	36.7	W
Power Dissipation-Derate above 25°C		0.29	W/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.4	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On/Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C I_D=1mA	-	0.04	-	V/°C
Drain-Source Leakage Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V, T_J=25°C	-	-	1	μA
		V_{DS}=24V, V_{GS}=0V, T_J=125°C	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	4.7	5.5	mΩ
		V_{GS}=4.5V, I_D=10A	-	6.3	8.5	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250uA	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	-4	-	mV/°C
Forward Transconductance	g_{fs}	V_{DS}=10V, I_D=10A	-	10	-	S
Dynamic and Switching Characteristics						
Total Gate Charge[3,4]	Q_g	V_{DS}=15V, I_D=20A V_{GS}=10V	-	24.6	49	nC
Gate-Source Charge[3,4]	Q_{gs}		-	1.85	3.7	
Gate-Drain Charge[3,4]	Q_{gd}		-	6.8	13	
Turn-On Delay Time[3,4]	$t_{d(on)}$	V_{DD}=15V, R_G=3.3Ω V_{GS}=10V, I_D=15A	-	7.5	15	nS
Rise Time[3,4]	t_r		-	14.5	28	
Turn-Off Delay Time[3,4]	$t_{d(off)}$		-	35.2	60	
Fall Time[3,4]	t_f		-	9.6	19	
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, F=1MHz	-	1160	1900	pF
Output Capacitance	C_{oss}		-	200	400	
Reverse Transfer Capacitance	C_{rss}		-	180	360	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	-	2.5	5	Ω
Guaranteed Avalanche Energy						
Single Pulse Avalanche Energy	E_{AS}	V_{DD}=25V, L=0.1mH, I_{AS}=20A	20	-	-	mJ
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	-	-	64	A
Pulsed Source Current[3]	I_{SM}		-	-	128	A
Diode Forward Voltage[3]	V_{SD}	V_{GS}=0V, I_S=1A, T_J=25°C	-	-	1	V
Reverse Recovery Time	t_{rr}	V_{GS}=0V, I_S=10A di/dt=100A/μs T_J=25°C	-	115	-	nS
Reverse Recovery Charge	Q_{rr}		-	148	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=42A, R_G=25Ω, starting T_J=25°C.
3. Pulse test: pulse width≤300us,duty cycle ≤2%.
4. Essentially independent of operation temperature.

Typical Electrical and Thermal Characteristic Curves

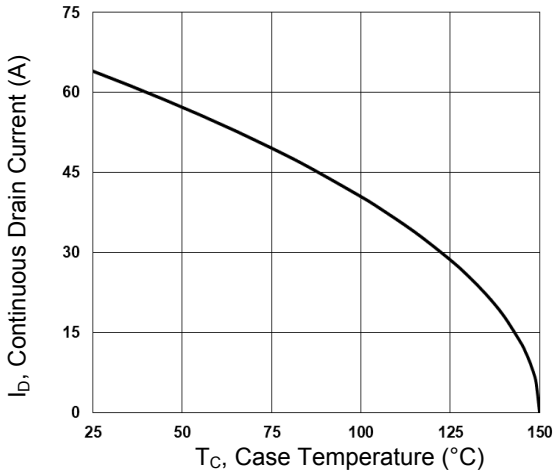


Figure 1. Continuous Drain Current vs. T_C

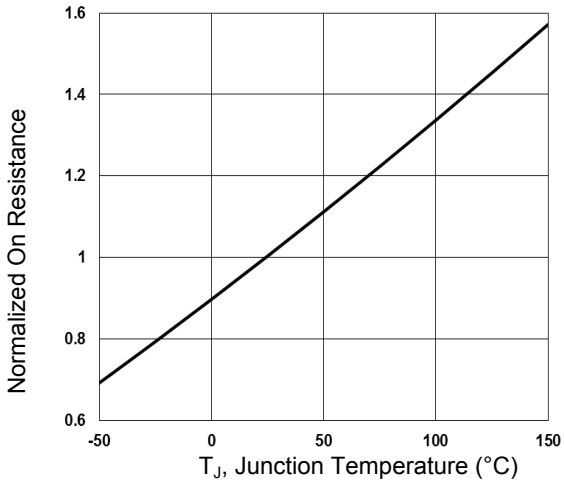


Figure 2. Normalized $R_{DS(ON)}$ vs. T_J

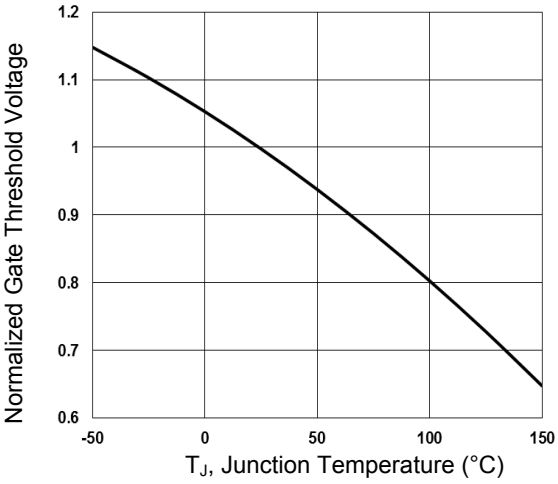


Figure 3. Normalized V_{th} vs. T_J

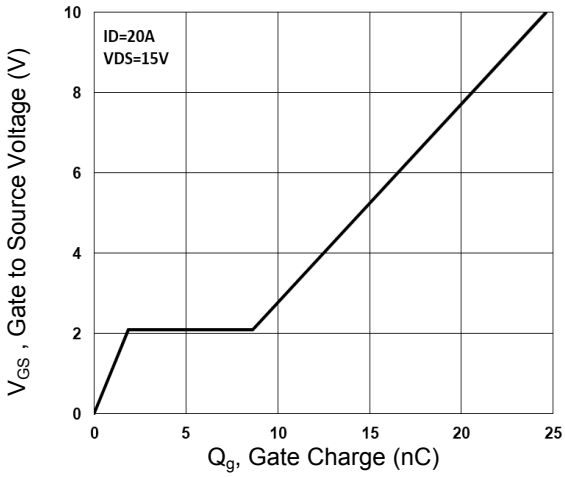


Figure 4. Gate Charge Characteristics

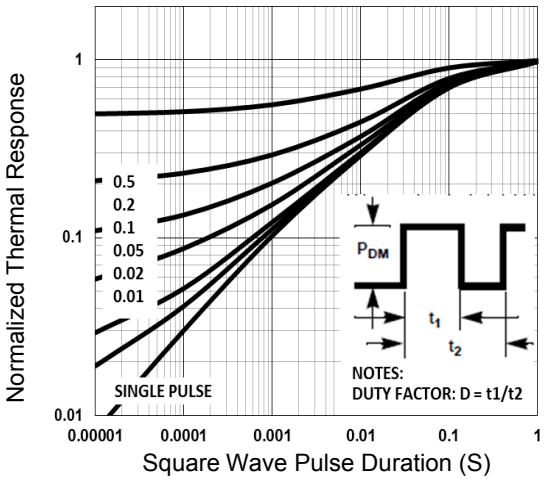


Figure 5. Normalized Transient Impedance

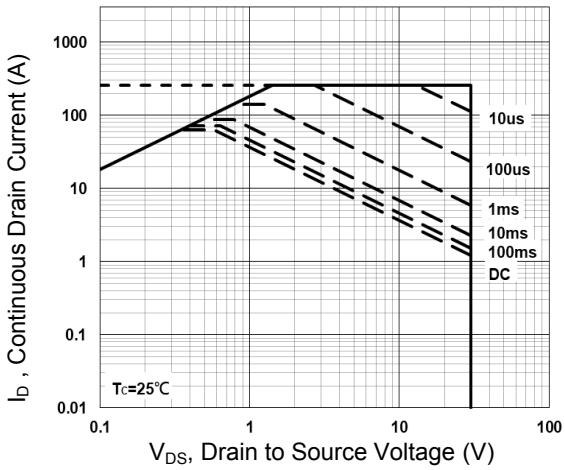


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

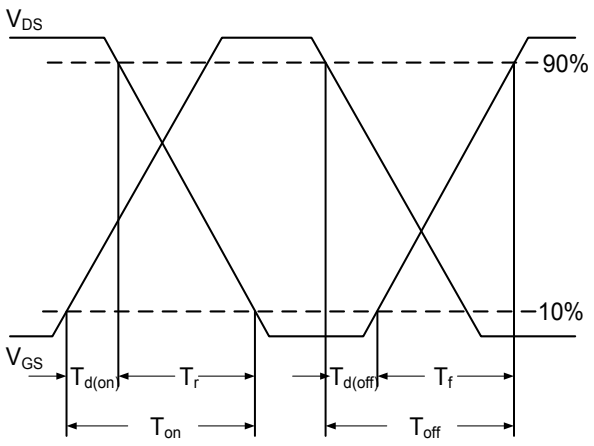


Figure 7. Switching Time Waveform

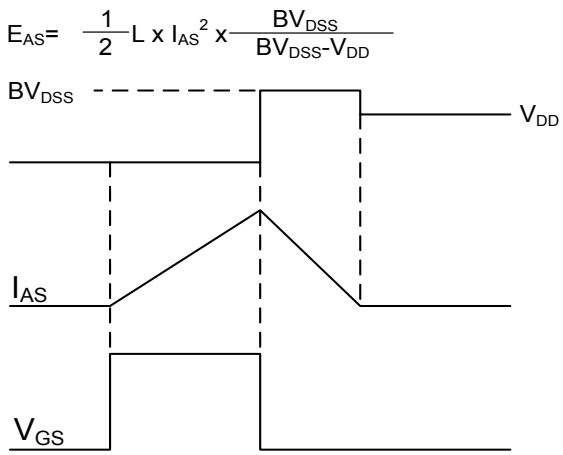
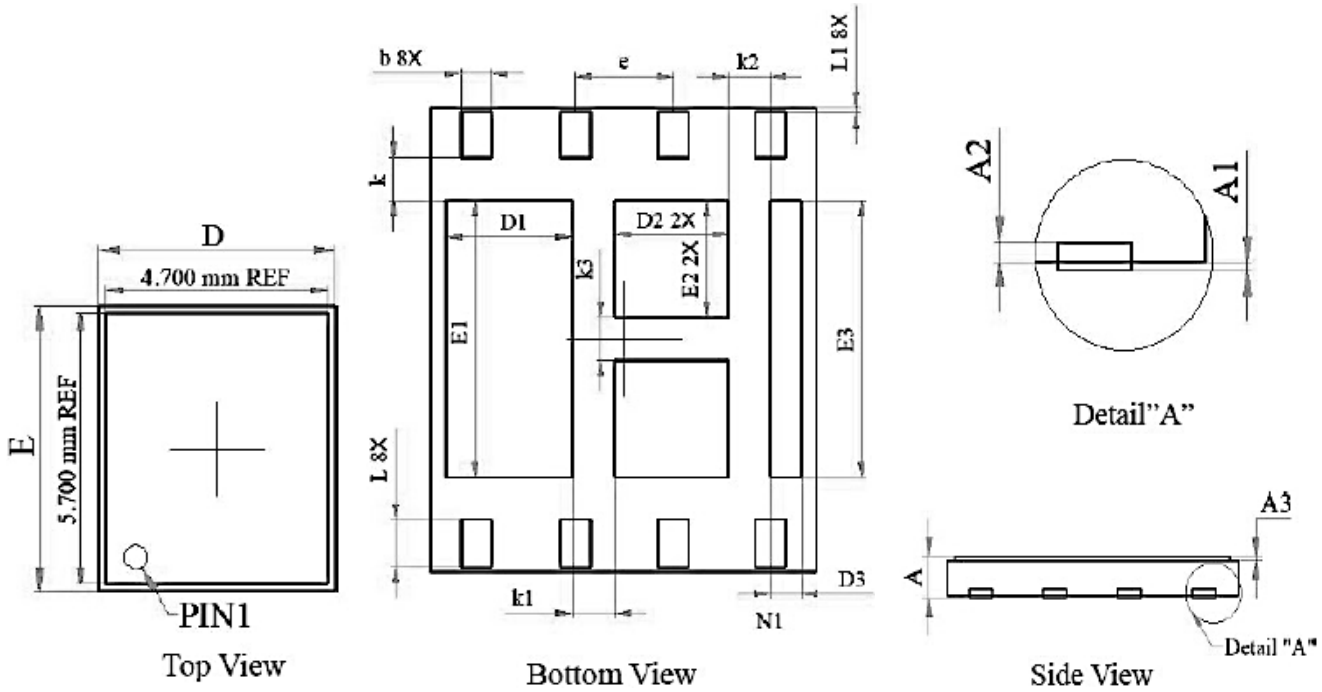


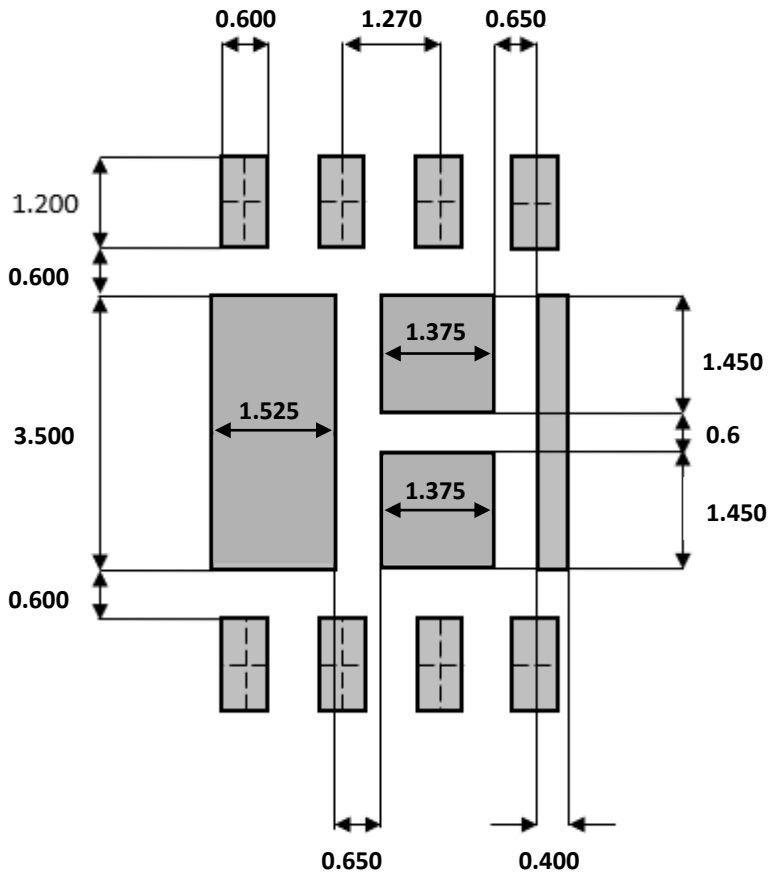
Figure 8. EAS Waveform

Package Outline Dimensions DFN5x6



Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters		
	MIN	Normal	MAX		MIN	Normal	MAX
A	0.530	-	0.600	D3	0.300	0.400	0.500
A1	-	-	0.005	E3	3.500	3.600	3.700
A2	0.030	-	0.100	b	0.350	0.400	0.450
A3	0.050	-	0.100	L	0.550	0.600	0.650
D	4.900	5.000	5.100	L1	0.010	0.050	0.090
E	5.900	6.000	6.100	k	0.550 REF		
D1	1.525	1.625	1.725	k1	0.550 REF		
E1	3.500	3.600	3.700	k2	0.550 REF		
D2	1.375	1.475	1.575	k3	0.550 REF		
E2	1.425	1.525	1.625	e	1.27 BSC		

Recommended Pad Layout



(Unit in MM)